ETR02054-001

Voltage monitoring IC for rechargeable batteries with CV charging. (Release Voltage 2.45V, Hysteresis width 0.35V~0.85V, Ultra low power Voltage Detector.)

### ■GENERAL DESCRIPTION

The XC6142 series are battery voltage monitoring ICs optimal to CV rechargeable batteries and electric double layer capacitors.

By setting release voltage to 2.45V and increasing the hysteresis width, it is possible to continue to output the release signal even in the voltage drop of the rechargeable batteries with high internal impedance due to inrush current. When the battery voltage drops, it is possible to make the subsequent system stop and stand by on the rear stage until the

charging is completed by setting the output signal at detection state.

In addition, hysteresis width is selectable in the range from 0.35V to 0.85V. So based on the internal impedance or over discharge voltage of a rechargeable battery, hysteresis width can be decided.

The SSOT-24 as well as ultra-small and low profile package USPQ-4B05 are available contributing to miniaturization of portable devices and high densely mounting applications.

Even when V<sub>IN</sub> voltage is lower than the minimum operating voltage, malfunction of the system can be avoided by the undefined operation prevention function which minimizes the rise of output voltage.

### APPLICATIONS

- Voltage monitoring for rechargeable batteries with CV charging.
- Voltage monitoring for electric double layer capacitors

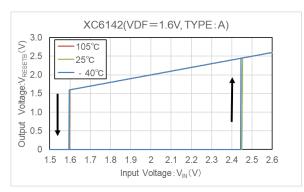
## FEATURES

**Operating Voltage Range** :1.1V~6.0V **Release Voltage** :2.45V **Detect Voltage** :1.6V ~ 2.1V (0.1V increments) Release Voltage Accuracy :±1.3% (Ta=25°C) ±2.0% (Ta=-40°C~ 105°C) **Detection Voltage Accuracy** :±0.8% (Ta=25°C) : ±2.5% (Ta=-40°C~ 105°C) **Temperature Characteristics** :±50ppm/°C (TYP.) Ultra-Low Power :104nA TYP.(@detect, V<sub>DF</sub>=1.6V, V<sub>IN</sub>=1.44V) 139nA TYP.(@release, VIN=2.7V) Output type : CMOS Nch open drain Output logic : RESETB (Active Low) **RESET** (Active High) Undefined operation : Output pin Voltage 0.38V (MAX: Ta=-40°C~105°C) Protection @Power supply Input pin Voltage (CMOS Output only) Operating voltage (MIN.) **Operating Ambient Temperature** :-40°C ~ 105°C Packages : USPQ-4B05 (1.0 x 1.0 x 0.33mm) SSOT-24 (2.0 x 2.1 x 1.1mm)

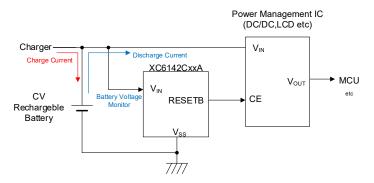
Environment friendly

### ■TYPICAL PERFORMANCE CHARACTERISTICS

:EU RoHS Compliant, Pb Free

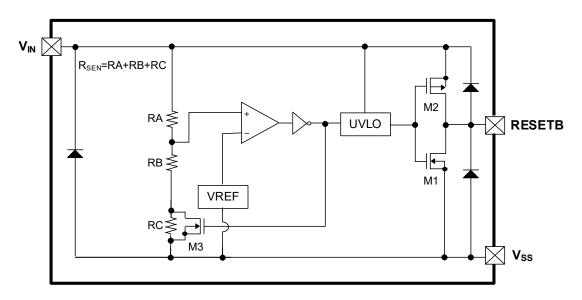


# ■TYPICAL APPLICATION CIRCUIT



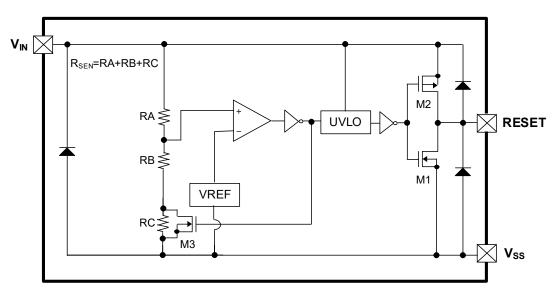
### ■BLOCK DIAGRAMS

(1) XC6142C Series A type (RESETB OUTPUT : CMOS output / Active Low)



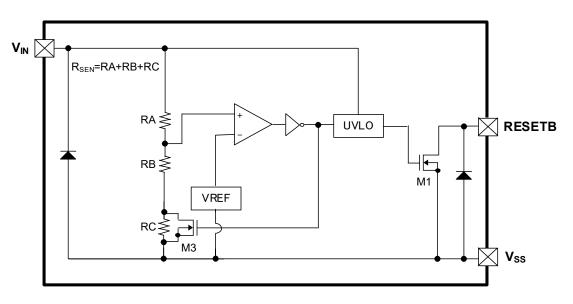
\* Diodes inside the circuits are ESD protection diodes and parasitic diodes.

(2) XC6142C Series C type (RESET OUTPUT : CMOS output / Active High)



\* Diodes inside the circuits are ESD protection diodes and parasitic diodes.

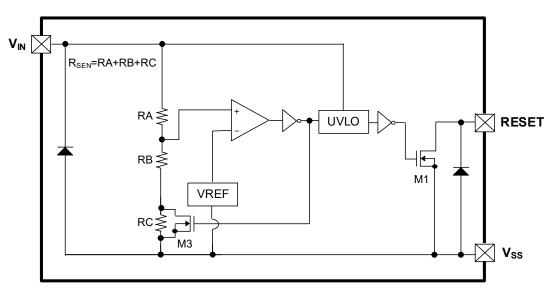
### ■BLOCK DIAGRAM



(3) XC6142N Series A type (RESETB OUTPUT : Noch open drain output / Active Low)

\* Diodes inside the circuits are ESD protection diodes and parasitic diodes.

(4) XC6142N Series C type (RESET OUTPUT : Nch open drain output / Active High)



\* Diodes inside the circuits are ESD protection diodes and parasitic diodes.

# ■PRODUCT CLASSIFICATION

#### Ordering Information

#### XC6142123456-7

DESIGNATOR	ITEM	SYMBOL	DESCRIPTION
1	Output	С	CMOS output
U	Configuration	N	Nch open drain output
23	Detect Voltage 16 ~ 21		e.g. 1.6V → ②=1, ③=6 * 0.1V increments
4	Turno	A	Refer to Selection Guide
4	Туре	С	
56-7 <sup>(*1)</sup>	Packages	9R-G	USPQ-4B05 (5,000pcs/Reel)
	(Order Unit)	NR-G	SSOT-24 (3,000pcs/Reel)

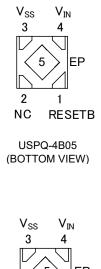
("1) The "-G" suffix denotes Halogen and Antimony free as well as being fully EU RoHS compliant.

#### •Selection Guide

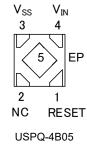
Туре	RESET OUTPUT	OUTPUT PIN NAME	DESCRIPTION		
А	Active Low	RESETB	Output Low level in detection state.		
С	Active High	RESET	Output High level in detection state.		

### **■**PIN CONFIGURATION

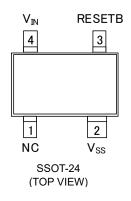


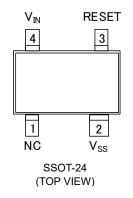


Type:C



(BOTTOM VIEW)





## ■ PIN ASSIGNMENT

PIN NUMBER			FUNCTIONS			
USPQ-4B05	SSOT-24	PIN NAME	FUNCTIONS			
1	RESETB		Reset Output (Active Low)			
I	3	RESET	Reset Output (Active High)			
2	1	NC	No Connection			
3	2	V <sub>SS</sub>	Ground			
4	4	VIN	Power Supply Input			
5 -		EP	Exposed thermal pad.			
			The Exposed pad is recommended to be connected to $V_{SS}$ (Pin3)			

## ■LOGIC CHART

	OUTPUT		Reset Output					
TYPE	Configuration	Release State	Detection State	Undefined State				
	Conngulation	Nelease State	/UVLO operating State	(VIN≦V <sub>INL</sub> :0.4V)				
	Nah anan drain	"H"	"L"	"H"				
А	Nch open drain	(Vpull : High impedance)	(GND : Low Impedance)	(Vpull : High impedance)				
A	CMOS	"H"	"L"	V <sub>UNO</sub>				
	CIVIOS	(VIN)	(GND)	(TYP. 0.1V)				
	Nch open drain	"L"	"H"	"Н"				
С	Non open drain	(GND : Low Impedance)	(Vpull : High impedance)	(Vpull : High impedance)				
C	CMOS	"L"	"H"	Undefined				
	CIVIOS	(GND)	(VIN)	Undelined				

# ■ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL		RATINGS	UNITS
Input Vo	Input Voltage		ÎN	-0.3 ~ 7.0	V
Output Voltage	XC6142C	V	V	$V_{SS}$ - 0.3 ~ $V_{IN}$ + 0.3 or 7.0 $^{(*1)}$	V
Output Voltage	XC6142N	V <sub>RESETB</sub>	Vreset	V <sub>SS</sub> - 0.3 ~ 7.0	V
Output Current	XC6142C	1	I	±50	m (
Output Current	XC6142N	IRBOUT	IROUT	50	mA
Power Dissipation	USPQ-4B05	P	d	550 (40mm x 40mm Standard board) (*2)	mW
(Ta=25℃)	SSOT-24		u	680 (JESD51-7 board) <sup>(*2)</sup>	TIVV
Junction Temperature		Tj		-40 ~ 125	°C
Storage Temperature		Tstg		-55 ~ 125	°C

\* All voltages are described based on the Vss.

 $^{(^{\star}1)}$  The maximum value should be either V\_IN+0.3V or 7.0V in the lowest.

 $\ensuremath{^{(^{*2})}}$  The power dissipation figure shown is PCB mounted and is for reference only.

Please refer to PACKAGING INFORMATION for the mounting condition.

### ■RECOMMENDED OPERATING CONDITIONS

PARAM	SYMBOL	MIN.	TYP.	MAX.	UNITS	
V <sub>IN</sub> Pin	VIN	2.2	-	6.0	V	
Neb open drein	Pull-up Voltage	Vpull	0.0	-	6.0	V
Nch open drain	Pull-up Resistance	R <sub>pull</sub>	10	100	-	kΩ
Operating Ambie	Topr	-40	-	105	°C	

 $^{\ast}$  Each voltage operating condition is based on Vss.

## ■ELECTRICAL CHARACTERISTICS

	0.445.01			Ta=25°C		-40°C	≦Ta≦10	05°C <sup>(*6)</sup>		
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	UNITS	CIRCUIT
Operating Voltage	Vin		1.1		6.0	1.1		6.0	V	
MIN Voltage Holding the Detection <sup>(*3)</sup> (CMOS output)	V <sub>INL</sub>		-	-	0.4	-	-	0.4	V	
Detect Voltage	Vdf	V <sub>DF(T)</sub> <sup>(*1)</sup> =1.6V~2.1V	V <sub>DF(T)</sub> ×0.992	V <sub>DF(T)</sub>	V <sub>DF(T)</sub> ×1.008	V <sub>DF(T)</sub> ×0.975	V <sub>DF(T)</sub>	V <sub>DF(T)</sub> ×1.025	v	1
Release Voltage	Vdr		2.418	2.45	2.482	2.401	2.45	2.499	v	
Detect Voltage Temperature Characteristics	ΔV <sub>DF</sub> / (ΔTopr•V <sub>DF</sub> )		-	±50	-	-	±50	-	ppm/°C	
Supply Current1 (CMOS output, A Type)							E-	2 <sup>(*2)</sup>		
Supply Current1 (CMOS output, C Type)	I <sub>ss1</sub>	$V_{IN} = V_{DF} \times 0.9$	$V_{IN} = V_{DF} \times 0.9$	-	E-	1 <sup>(*2)</sup>	-	E-3 <sup>(*2)</sup>		
Supply Current1 (Nch open drain output , A/C Type)							E-	4 <sup>(*2)</sup>	nA	2
Supply Current2 (CMOS output, A Type)							139	431	ΠA	Z
Supply Current2 (CMOS output, C Type)	I <sub>ss2</sub>	V <sub>IN</sub> = 2.7V	-	139	289	-	139	580		
Supply Current2 (Nch open drain output , A/C Type)							139	433		
Peak of Undefined Operation <sup>(*4)</sup> (CMOS output, A Type)	Vuno	V <sub>IN</sub> < 0.4V	-	0.1	0.38	-	0.1	0.38	V	3
UVLO Release Voltage	Vuvlor	V <sub>IN</sub> = 0V→1.1V	-	0.82	1.05 <sup>(*5)</sup>	-	0.82	1.07	v	
UVLO Detect Voltage	V <sub>UVLOD</sub>	V <sub>IN</sub> = 1.1V→0V	0.57 <sup>(*5)</sup>	0.79	-	0.55	0.79	-	v	
UVLO Release Delay Time	tuvlor	V <sub>IN</sub> = 0V→1.1V	-	157	290 <sup>(*5)</sup>	-	157	425	μs	-

(\*1) V<sub>DF(T)</sub>: Nominal detect voltage

(\*2) Refer to SPEC TABLE.

 $^{(^{\prime}3)}$  XC6142C (CMOS output) only. V\_{IN} value where RESETB < 0.05V or RESET > V\_{IN} - 0.05V.

(\*4) XC6142C (CMOS output) only.

 $^{(^{\ast}5)}$  The MIN. and MAX. specifications related to UVLO are setting values.

 $^{(^{*}6)}$  The ambient temperature range (-40°C  $\leq$  Ta  $\leq$  105°C) is a design value.

## ■ELECTRICAL CHARACTERISTICS

DADAMETED				Ta=25°C		-40°C	≦Ta≦10	5°C <sup>(*13)</sup>		
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	UNITS	CIRCUIT
Release Delay Time <sup>(*7)</sup>	t <sub>DR0</sub>	$V_{IN} = V_{DF} \times 0.9 \rightarrow V_{DF} \times 1.1$	-	44	200	-	44	224		<b>(4</b> )
Detect Delay Time <sup>(*8)</sup>	t <sub>DF0</sub>	$V_{IN} = V_{DF} \times 1.1 \rightarrow$ $V_{DF} \times 0.9$	-	40	170	-	40	184	μs	4
		Nch. V <sub>RESETB</sub> =0.3V								
	IRBOUTN	V <sub>IN</sub> =1.1V	0.3	1.4	-	0.2	1.4	-		
RESETB		V <sub>IN</sub> =2.0V <sup>(*9)</sup>	4.1	6.2	-	3.1	6.2	-	mA	
Output Current		Pch. V <sub>RESETB</sub> =V <sub>IN</sub> -0.3V							IIIA	
	I <sub>RBOUTP</sub> <sup>(*10)</sup>	V <sub>IN</sub> =3.0V	-	-3.2	-1.4	-	-3.2	-1.3		
		V <sub>IN</sub> =6.0V	-	-5.1	-2.9	-	-5.1	-2.6		
		Nch. V <sub>RESET</sub> =0.3V							mA	
	I <sub>routn</sub>	V <sub>IN</sub> =2.0V <sup>(*11)</sup>	4.1	6.2	-	3.1	6.2	-		
		V <sub>IN</sub> =3.0V	8.1	10.8	-	4.3	10.8	-		
RESET		V <sub>IN</sub> =4.0V	11.2	14.3	-	6.2	14.3	-		
Output Current		V <sub>IN</sub> =5.0V	13.7	17.1	-	7.3	17.1	-		
		V <sub>IN</sub> =6.0V	15.7	19.3	-	8.1	19.3	-		5
	(*10)	Pch. V <sub>RESET</sub> =V <sub>IN</sub> -0.3V	Pch. V <sub>RESET</sub> =V <sub>IN</sub> -0.3V					•		
	IROUTP <sup>(*10)</sup>	V <sub>IN</sub> =1.1V	-	-0.7	-0.2	-	-0.7	-0.15		
RESETB Output	I <sub>LEAKN</sub> <sup>(*12)</sup>	V <sub>IN</sub> =6.0V Nch. V <sub>RESETB</sub> =6.0V	-	0.01	0.1	-	0.01	0.3		
Leakage Current	ILEAKP	V <sub>IN</sub> =1.1V Pch. V <sub>RESETB</sub> =0V	-	-0.01	-	-	-0.01	-	μA	
RESET Output	Ileakn <sup>(*12)</sup>	V <sub>IN</sub> =1.1V Nch. V <sub>RESET</sub> =6.0V	-	0.01	0.1	-	0.01	0.3		
Leakage Current	I <sub>LEAKP</sub>	V <sub>IN</sub> =6.0V Pch. V <sub>RESET</sub> =0V	-	-0.01	-	-	-0.01	-		

<sup>(\*7)</sup> RESETB product: Time from when the V<sub>IN</sub> pin voltage reaches the release voltage until the reset output pin reaches V<sub>IN</sub>×90%. RESET product: Time from when the V<sub>IN</sub> pin voltage reaches the release voltage until the reset output pin reaches V<sub>IN</sub>×10%

<sup>('8)</sup> RESETB product: Time from when the  $V_{IN}$  pin voltage reaches the detect voltage until the reset output pin reaches  $V_{IN} \times 10\%$ .

RESET product: Time from when the  $V_{IN}$  pin voltage reaches the detect voltage until the reset output pin reaches  $V_{IN} \times 90\%$ . (\*9) Only for products with  $V_{DF(T)} \ge 2.1V$ .

(\*10) XC6142C (CMOS output) only.

(\*11) Only for products with  $V_{DF(T)} \leq 1.9V$ .

(\*12) Max. value is for XC6142N (Nch open drain).

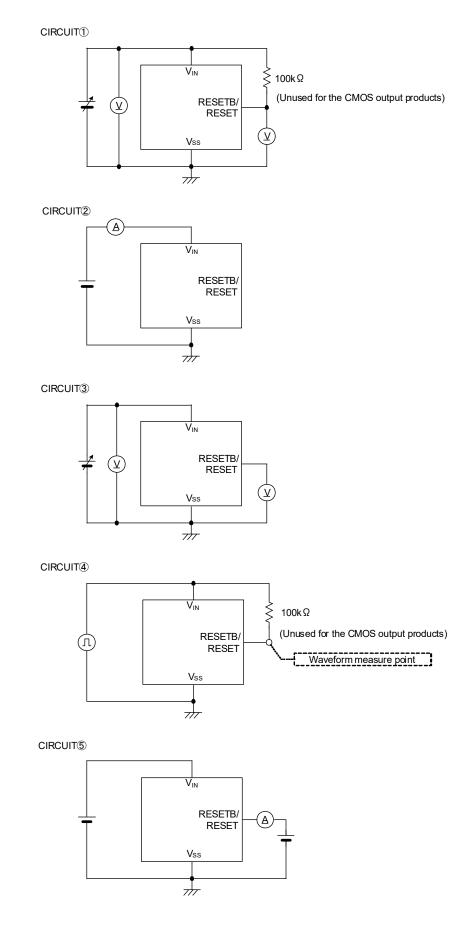
(\*13) The ambient temperature range (-40°C $\leq$ Ta $\leq$ 105°C) is a design value.

# ■ELECTRICAL CHARACTERISTICS (SPEC TABLE)

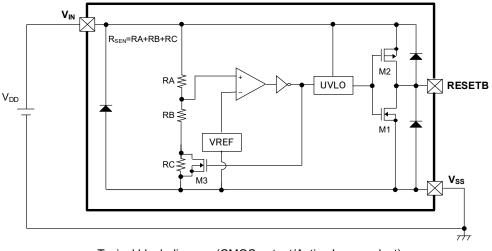
#### Table of Characteristics by Voltage Setting

NOMINAL	E	-1		-2	E	-3	E	-4
DETECT	Ta=	25°C		-	-40°C≦T	a≦105℃	;	
VOLTAGE(V)			S	upply Cu	rrent1 (n/	4)		
V <sub>DF(T)</sub>	TYP.	MAX.	TYP.	MAX.	TYP.	MAX.	TYP.	MAX.
1.6	104	235	104	457	104	351	104	364
1.7	108	240	108	464	108	357	108	371
1.8	111	245	111	471	111	363	111	377
1.9	114	251	114	478	114	370	114	384
2.0	117	256	117	484	117	376	117	390
2.1	121	262	121	491	121	383	121	397

# ■TEST CIRCUITS



### OPERATIONAL DESCRIPTION (Active Low)



Typical block diagram (CMOS output/Active Low product)

The circuit operation in the above representative circuit example will be explained using the timing chart.

#### ③ (③') Detection state

The RESETB pin will hold "L" until the  $V_{IN}$  pin voltage becomes equal to or greater than the release voltage ( $V_{DR}$ ).

#### $(3) \rightarrow (4)$ Transition from detection state to released state

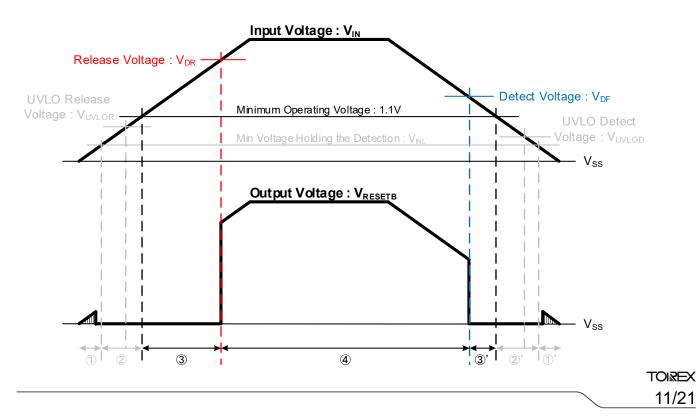
When the  $V_{IN}$  pin voltage reaches the release voltage ( $V_{DR}$ ), the circuit will determine that the monitoring voltage has exceeded the release level. After the release delay time ( $t_{DR0}$ ) has passed, it will turn M3 OFF and output "H" to the RESETB pin.

#### ④ Released state

The RESETB pin will hold "H" until the V<sub>IN</sub> pin voltage becomes equal to or less than the detection voltage (V<sub>DF</sub>).

#### $(4) \rightarrow (3)$ ' Transition from released state to detection state

When the  $V_{IN}$  pin voltage reaches the detection voltage ( $V_{DF}$ ), the circuit will determine that the monitoring voltage has fallen below the detection level. After the detect delay time ( $t_{DF0}$ ) has passed, it will turn M3 ON and output "L" to the RESETB pin.



## ■OPERATIONAL DESCRIPTION (Active Low)

- Operation below Minimum Operating Voltage
  - (2)(2)') Detection holding state

If the  $V_{IN}$  pin voltage is equal to or greater than the minimum voltage holding the detection ( $V_{INL}$ ), the operation of the UVLO function will cause the RESETB pin to maintain "L" (= detection state).

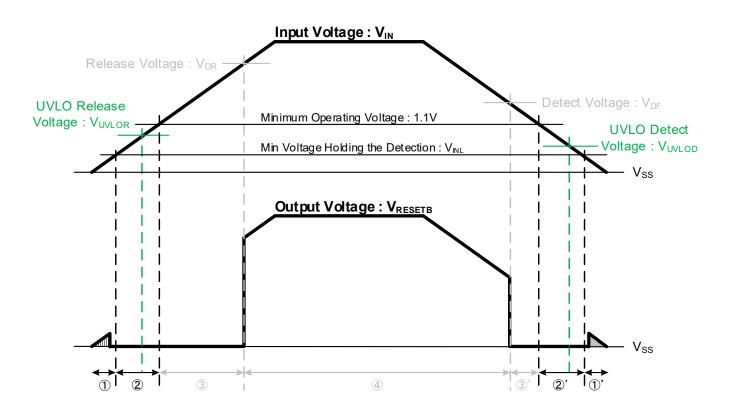
② Following the operation of the UVLO function, after the  $V_{IN}$  pin voltage reaches the UVLO release voltage ( $V_{UVLOR}$ ), the UVLO

function will be released once the UVLO release delay time (t<sub>UVLOR</sub>) has passed.

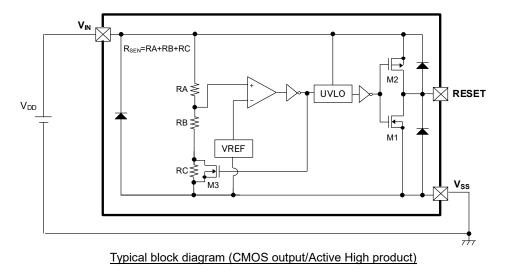
- ②' If the V<sub>IN</sub> pin voltage falls to the UVLO detect voltage (V<sub>UVLOD</sub>), the UVLO function will operate and the RESETB pin will maintain "L".
- ① (①') Undefined state

If the  $V_{IN}$  pin voltage is less than the minimum voltage holding the detection ( $V_{INL}$ ), the UVLO function will not be able to operate properly, and the RESETB pin will be in an undefined state.

\* The above operation description is for CMOS output products, but for Nch open drain products, the pull-up destination voltage will be output to the RESETB pin until FET M1 becomes ON state.



### OPERATIONAL DESCRIPTION (Active High)



The circuit operation in the above representative circuit example will be explained using the timing chart.

#### (3) (3) Detection state

The RESET pin will hold "H" until the V<sub>IN</sub> pin voltage becomes equal to or greater than the release voltage (V<sub>DR</sub>).

#### $(3) \rightarrow (4)$ Transition from detection state to released state

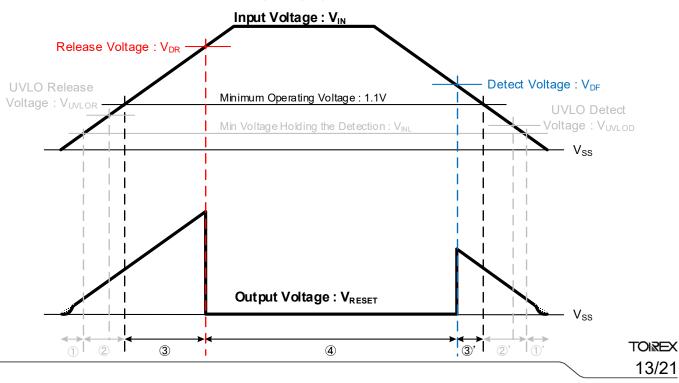
When the V<sub>IN</sub> pin voltage reaches the release voltage (V<sub>DR</sub>), the circuit will determine that the monitoring voltage has exceeded the release level. After the release delay time ( $t_{DR0}$ ) has passed, it will turn M3 OFF and output "L" to the RESET pin.

#### ④ Released state

The RESET pin will hold "L" until the  $V_{IN}$  pin voltage becomes equal to or less than the detection voltage ( $V_{DF}$ ).

#### $(4) \rightarrow (3)$ ' Transition from released state to detection state

When the  $V_{IN}$  pin voltage reaches the detection voltage ( $V_{DF}$ ), the circuit will determine that the monitoring voltage has fallen below the detection level. After the detect delay time ( $t_{DF0}$ ) has passed, it will turn M3 ON and output "H" to the RESET pin.



# OPERATIONAL DESCRIPTION (Active High)

Operation below Minimum Operating Voltage

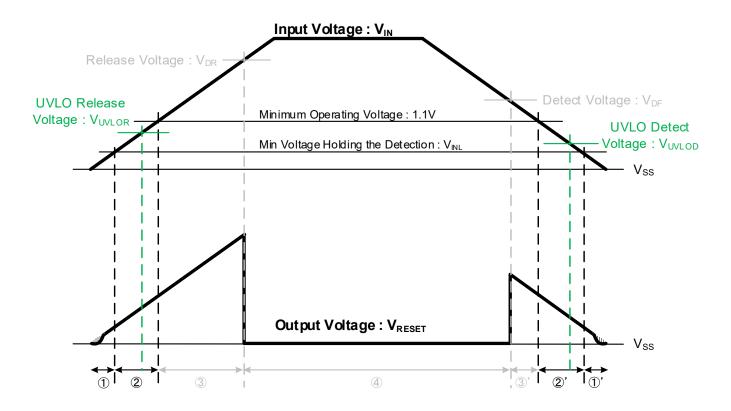
#### (2)(2)') Detection holding state

If the  $V_{IN}$  pin voltage is equal to or greater than the minimum voltage holding the detection ( $V_{INL}$ ), the operation of the UVLO function will cause the RESET pin to maintain "H" (= detection state).

- ② Following the operation of the UVLO function, after the  $V_{IN}$  pin voltage reaches the UVLO release voltage ( $V_{UVLOR}$ ), the UVLO function will be released once the UVLO release delay time ( $t_{UVLOR}$ ) has passed.
- ②' If the V<sub>IN</sub> pin voltage falls to the UVLO detect voltage (V<sub>UVLOD</sub>), the UVLO function will operate and the RESET pin will maintain "H".
- (1) (1)') Undefined state

If the  $V_{IN}$  pin voltage is less than the minimum voltage holding the detection ( $V_{INL}$ ), the UVLO function will not be able to operate properly, and the RESET pin will be in an undefined state.

\* The above operation description is for CMOS output products, but for Nch open drain products, the pull-up destination voltage will be output to the RESET pin until FET M1 becomes ON state.



### ■OPERATIONAL DESCRIPTION

<Select guide for pull-up resistor (Nch open drain)>

When an Nch open drain output is used, a pull-up resistor connected to the RESET/RESETB pin causes a deviation in the output voltage between the  $V_{SS}$  and Pull-up voltage.

To reduce the deviation in the output voltage between the V<sub>SS</sub> and Pull-up voltage, connect a pull-up resistor of around  $10k\Omega$  to several  $100k\Omega$ .

If the resistance value of pull-up resistor is small, the deviation from  $V_{SS}$  becomes large and it is impossible to meet the "L" voltage of the MCU.

Similarly, if the resistance value of pull-up resistor is large, the deviation from V<sub>pull</sub> becomes large and it is impossible to meet the "H" voltage. In the actual specifications, select a pull-up resistor that meets the logic threshold of the subsequent IC.

Below is an example calculation of the maximum output "L" voltage and the minimum output "H" voltage with Active Low product.

[Maximum value of output "L" voltage]

 $V_{\text{RESETB}} = V_{\text{pull}} / (1 + R_{\text{pull}} / R_{\text{ON}_{\text{MAX}}})$ 

 $\begin{array}{ll} V_{\text{pull}} & & \\ Pull-up \ voltage \\ R_{\text{ON}\_\text{MAX}} & & \\ \end{array} \\ \begin{array}{ll} On \ resistor \ maximum \ value \ of \ Nch \ driver \ M1. \end{array}$ 

2. Calculation of V<sub>RESETB</sub> Calculate the maximum value of the output "L" voltage using R<sub>ON\_MAX</sub>.  $V_{RESETB} = V_{pull} / (1 + R_{pull} / R_{ON_MAX}) = 1.8V / (1 + 10k\Omega / 73\Omega) \Rightarrow 13mV$ 

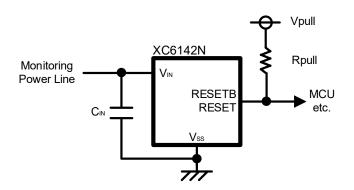
[Minimum value of output "H" voltage]

 $\begin{array}{ll} V_{\text{RESETB}} = V_{\text{pull}} - R_{\text{pull}} \times I_{\text{LEAKN}_{MAX}} \\ V_{\text{pull}} & : \text{Pull-up voltage} \\ I_{\text{LEAKN}_{MAX}} & : \text{Leakage current maximum value of Nch driver M1.} \end{array}$ 

Calculation Example) V<sub>pull</sub>=6.0V, R<sub>pull</sub>=100kΩ

- Calculation of I<sub>LEAKN\_MAX</sub> Calculated from the electrical characteristics based on I<sub>LEAKN\_MAX</sub> = 0.1μA (MAX.)
- 2. Calculation of VRESETB

Calculate the minimum value of the output "H" voltage using I<sub>LEAKN\_MAX</sub>.  $V_{RESETB} = V_{pull} - R_{pull} \times I_{LEAKN_MAX} = 6.0V - 100k\Omega \times 0.1\mu A = 5.99V$ 



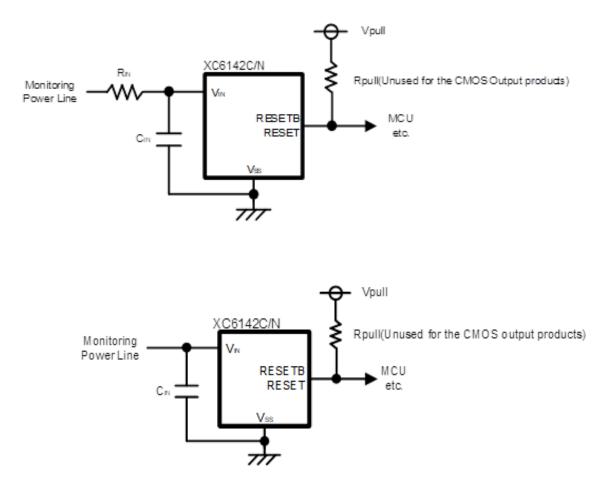
Pull-up resistance (Nch Open Drain)

### ■NOTES ON USE

- (1) Please use this IC within the stated maximum ratings. For temporary, transitional voltage drop or voltage rising phenomenon, the IC is liable to malfunction should the ratings be exceeded. Also, if used under out of the recommended operating range, the IC may not operate normally or may cause deterioration.
- (2) Factors such as the V<sub>IN</sub> pin voltage slope, surrounding components, or noise from external sources may cause the conditions indicated in (a) ~ (c) below to occur.

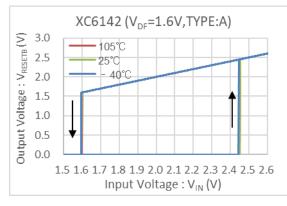
If these conditions occur, carry out measures such as inserting a capacitor ( $C_{IN}$ ) between  $V_{IN}$  and  $V_{SS}$ , if necessary. (Indicated in the following diagram.)

- (a) If a resistance (R<sub>IN</sub>) is inserted between the power supply and V<sub>IN</sub> pin, the V<sub>IN</sub> pin voltage may drop due to the flow-through current and resistance (R<sub>IN</sub>) generated during detection and release.
   In addition, with CMOS output products the drop in V<sub>IN</sub> pin voltage may become larger due to the output current. This temporary drop in V<sub>IN</sub> pin voltage may cause oscillation of the output and malfunctions.
- (b) If the VIN pin voltage has a steep slope, it may cause the output voltage to float or other such unstable operation to occur.
- (c) Power supply noise from external sources may cause IC malfunctions.
- (3) Torex places an importance on improving our products and their reliability. We request that users incorporate fail-safe designs and post-aging protection treatment when using Torex products in their systems.

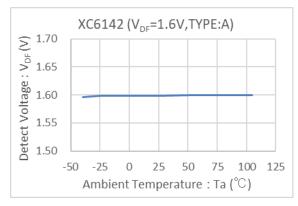


# ■TYPICAL PERFORMANCE CHARACTERISTICS

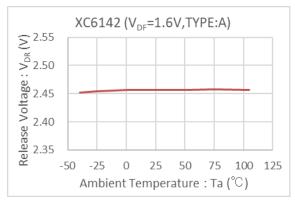
#### (1) Output Voltage vs. Input Voltage



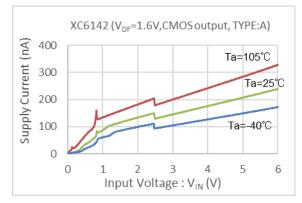
(2) Detect Voltage vs. Ambient Temperature

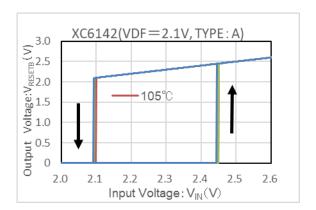


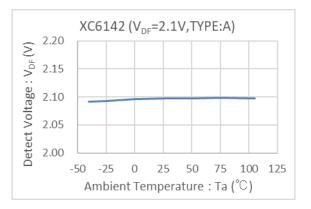
#### (3) Release Voltage vs. Ambient Temperature

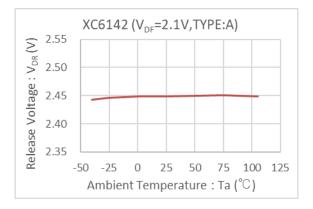


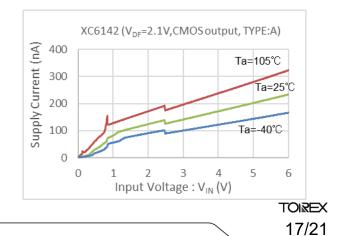
(4) Supply Current vs. Input Voltage





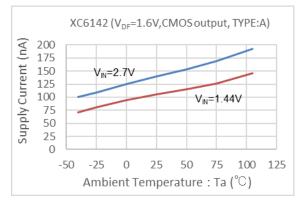




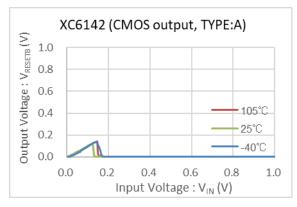


# TYPICAL PERFORMANCE CHARACTERISTICS

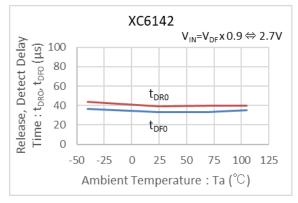
#### (5) Supply Current vs. Ambient Temperature

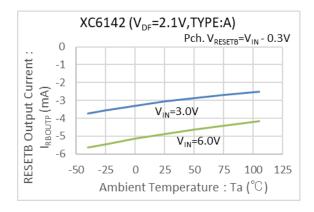


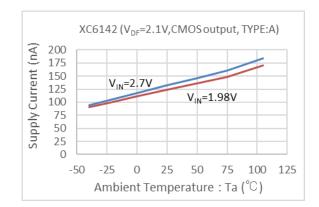
(6) Output Voltage vs. Input Voltage ( $V_{IN}$ <br/>Operating Voltage)

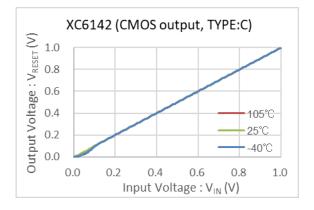




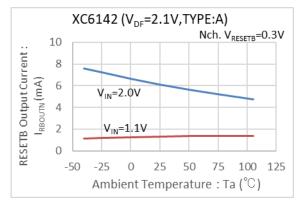




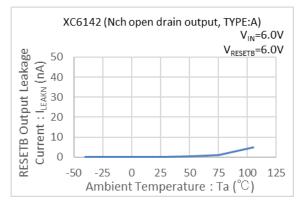




(8) RESETB Output Current vs. Ambient Temperature



(9) RESETB Output Leakage Current vs. Ambient Temperature



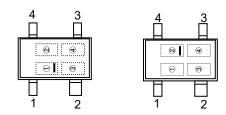
# ■PACKAGING INFORMATION

For the latest package information go to, <u>www.torexsemi.com/technical-support/packages</u>

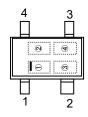
PACKAGE	OUTLINE / LAND PATTERN	THERMAL CHARACTERISTICS
SSOT-24	SSOT-24 PKG	SSOT-24 Power Dissipation
USPQ-4B05	USPQ-4B05 PKG	USPQ-4B05 Power Dissipation

### MARKING RULE

SSOT-24 (with underline mark)

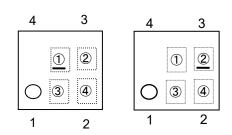


SSOT-24 (with overline mark)

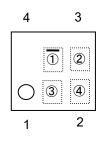


1 represents products series

#### USPQ-4B05 (with underline mark)



USPQ-4B05 (with overline mark)



	MARK	Registration order	PRODUCT SERIES
<u>X</u>	(with underline)	1	
1	(with overline)	2	
3	(with overline)	3	
5	(with overline)	e) 4	XC6142*****-G
А	(no line)	5	XC0142 -G
В	(no line)	6	
С	(no line)	7	
С	(no line)	8	

\*Mark 1 is a common symbol and Mark 2 is assigned a sequential number.

2	represents	internal	sequential	number
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	MARK ①	MARK (2)
<u>X</u>	(with under line)	No line
1	(with over line)	No line
3	(with over line)	No line
5	(with over line)	No line
А	(no line)	Under line
В	(no line)	Under line
С	(no line)	Under line
D	(no line)	Under line

0~9, A~Z repeated. (G, I, J, O, Q, W excluded)

③,④ represents production lot number
01~09, 0A~0Z, 11~9Z, A1~A9, AA~A9, AA~Z9 repeated.
(G, I, J, O, Q, W excluded)

TOIREX 21/21

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